

FEATURES

- 2.80 mm X 1.30 mm active area
- Low capacitance
- Long term stability
- High NIR sensitivity

DESCRIPTION

3.6 mm² Low Capacitance PIN Photodiode. Hermetically packaged in a TO-52 with a clear borosilicate glass window cap.

APPLICATIONS

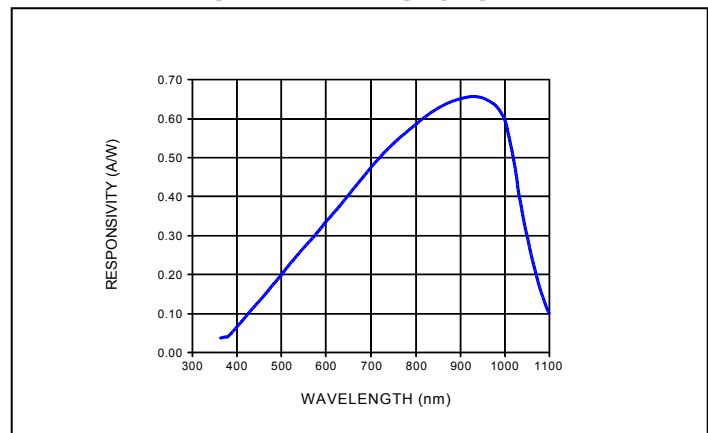
- Laser detection
- Instrumentation
- Optical remote control
- Pulsed light sensor



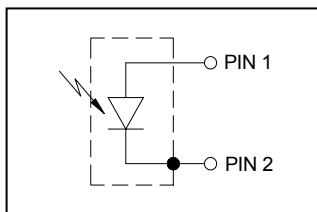
ABSOLUTE MAXIMUM RATING

| SYMBOL | PARAMETER | MIN | MAX | UNITS |
|---------------------|---------------------------|-----|------|-------|
| T _{STG} | Storage Temp | -55 | +125 | °C |
| T _{OP} | Operating Temp | -40 | +100 | °C |
| V _{R(OP)} | Reverse Operating Voltage | - | 50 | V |
| I _(PEAK) | Peak DC Current | - | 10 | mA |

SPECTRAL RESPONSE



SCHEMATIC



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|-----------------|------------------------|--|-----|-------------------------|-----|---------------------|
| I _D | Dark Current | V _R = 12 V | --- | 1.0 | --- | nA |
| C | Capacitance | V _R = 12 V | --- | 5.0 | --- | pF |
| | Responsivity | V _R = 0 V; λ = 950 nm | --- | 0.65 | --- | A/W |
| | | V _R = 0 V; λ = 1064 nm | --- | 0.20 | --- | |
| NEP | Noise Equivalent Power | V _R = 12 V; λ = 850 nm; R _L = 50 Ω | --- | 1.5 × 10 ⁻¹⁴ | --- | W/Hz ^{1/2} |
| V _{BR} | Breakdown Voltage | I _R = 10 μA | 30 | --- | --- | V |
| t _r | Rise Time | V _R = 12 V; λ = 850 nm; R _L = 50 Ω | --- | 45 | --- | ns |

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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